



# LA6584M

Monolithic Linear IC  
**BTL Driver Single-Phase Full-Wave  
 Fan Motor Driver**

## Overview

The LA6584M is Single-phase bipolar fan motor is put into silent driving by means of BTL output linear drive, offering high efficiency and power saving by suppressing the reactive current. Lock protection and rotation signal (FG, RD) circuits are built in, ensuring optimum application to small fans for notebook PC, consumer equipment power supply, car audio system, CPU cooler, etc. that require high reliability and low noise.

## Functions and Applications

- Single-phase full-wave driver for fan motor

## Specifications

**Absolute Maximum Ratings** at  $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Output voltage	$V_{CC}$ max		15	V
Allowable dissipation	$P_d$ max	Mounted on a specified board*	1.5	W
Output current	$I_{OUT}$ max		1.6	A
Output withstand voltage	$V_{OUT}$ max		15	V
RD/FG output pin output Withstand voltage	VRD/FG max		15	V
RD/FG output current	IRD/FG max		5	mA
HB output voltage	IB max		10	mA
Operating temperature	$T_{opr}$		-30 to +90	$^\circ\text{C}$
Storage temperature	$T_{stg}$		-55 to +150	$^\circ\text{C}$

\*Mounted on a specified board (114.3×76.1×1.6mm, Glass epoxy)

**Recommended Operating Range** at  $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage	$V_{CC}$		2.8 to 14.0	V
Common-phase input voltage Range of Hall input	VICM		0 to $V_{CC}$ -1.5	V

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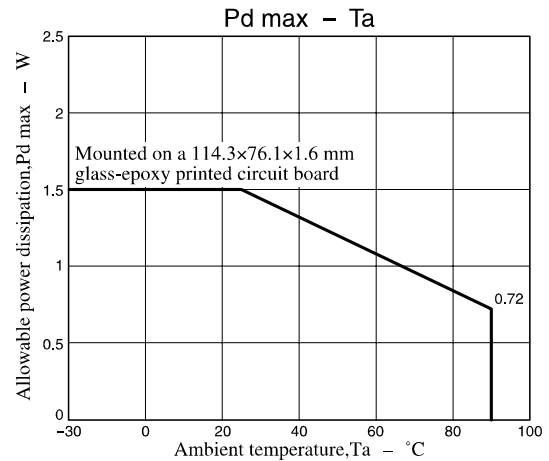
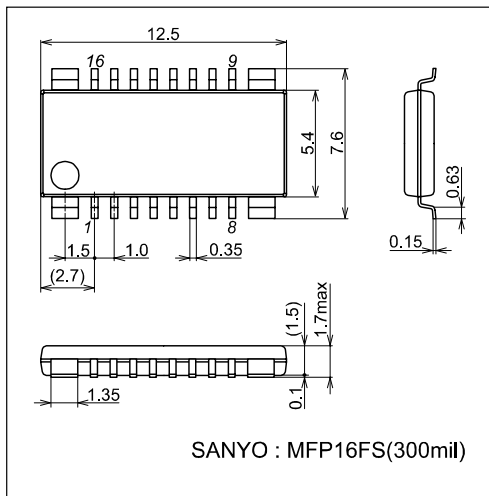
**Electrical Characteristics** at  $T_a = 25\text{ }^\circ\text{C}$ ,  $V_{CC} = 12\text{ V}$ , unless especially specified.

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Circuit current	$I_{CC1}$	During drive (CT = L)	4	6	9	mA
	$I_{CC2}$	During lock protection (CT = H)	2	4	6	mA
Lock detection capacitor charge current	$I_{CT1}$		2.0	2.8	3.5	$\mu\text{A}$
Capacitor discharge current	$I_{CT2}$		0.15	0.23	0.30	$\mu\text{A}$
Capacitor charge and discharge current ratio	RCT	$RCD = I_{CT1}/I_{CT2}$	9	12	15	-
CT charge voltage	VCT1		1.6	1.7	1.8	V
CT discharge voltage	VCT2		0.6	0.7	0.8	V
OUT output L saturation voltage	VOL	$I_O = 200\text{ mA}$		0.2	0.3	V
OUT output H saturation voltage	VOH	$I_O = 200\text{ mA}$		0.9	1.2	V
Hall input sensitivity	VHN	Zero peak value (including offset and hysteresis)		7	15	mV
RD/FG output pin L voltage	VRD/FG	$IRD/FG = 5\text{ mA}$		0.1	0.2	V
RD/FG output pin leak current	IRD/FGL	$VRD/FG = 15\text{ V}$		1	30	$\mu\text{A}$
HB output L voltage	VHBL	$IHB = 5\text{ mA}$	1.3	1.5	1.7	V

## Package Dimensions

unit : mm

3097B

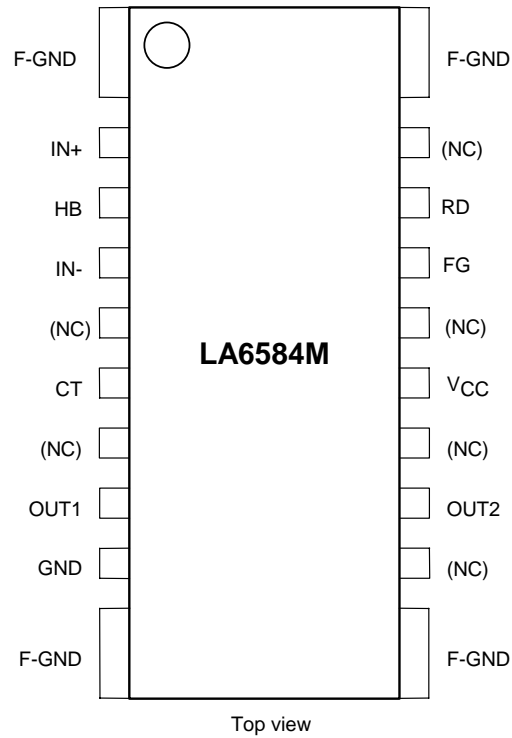


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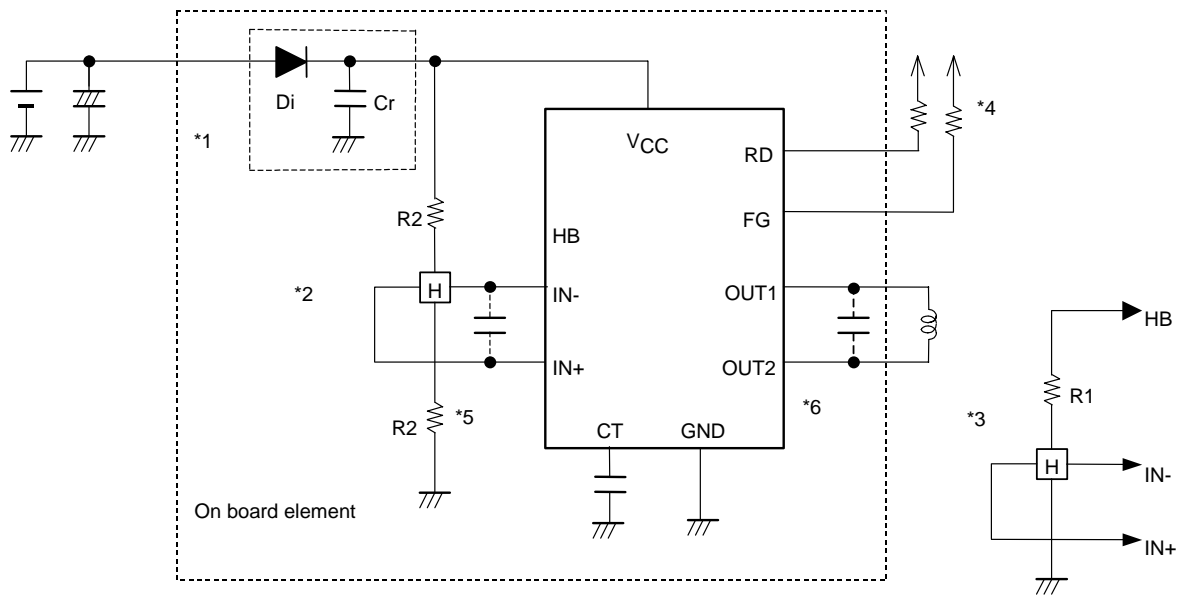
## Truth Table

IN-	IN+	CT	OUT1	OUT2	FG	RD	Mode
H	L	L	H	L	L	L	During rotation
L	H		L	H	H		
-	-	H	OFF	OFF	-	H	During overheat protection

## Pin Assignment

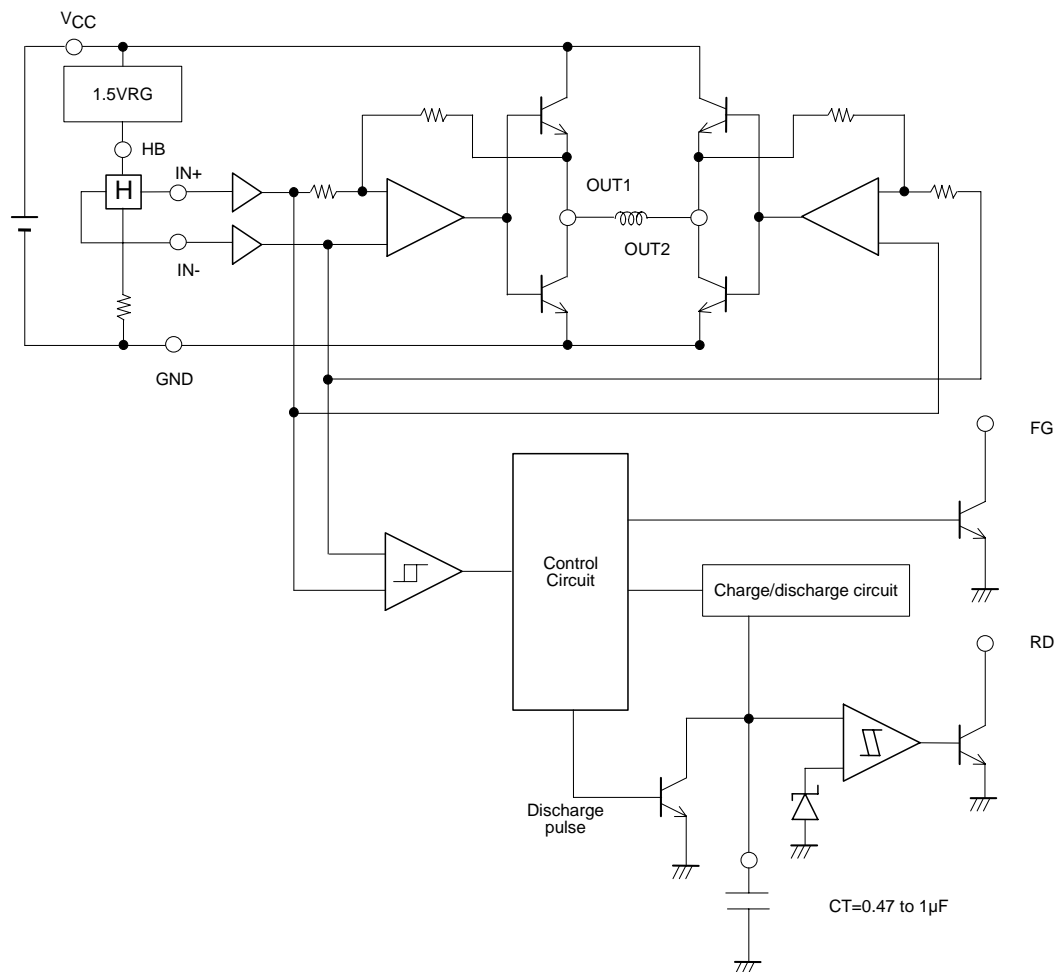


Sample Application Circuit



- \*1 When Di to prevent breakdown in case of reverse connection is used, it is necessary to insert a capacitor Cr to secure the regenerative current route. Similarly, Cr is necessary to enhance the reliability when there is no capacitor near the fan power line.
- \*2 To obtain Hall bias from V<sub>CC</sub>, carry out 1/2×V<sub>CC</sub> bias as shown in the figure. Linear driving is made through voltage control of the coil by amplifying the Hall output. When the Hall element output is large, the startup performance and efficiency are improved. Adjustment of the Hall element can reduce the noise further.
- \*3 When the Hall bias is taken from the HB pin, constant-voltage bias is made with about 2.0 V. Therefore, the Hall element can provide the output satisfactory in temperature characteristics. Adjustment of the Hall output amplitude is made with R1. (When V<sub>CC</sub> = 12 V, the step \*2 above proves advantageous for IC heat generation.)
- \*4 Keep this open when not used.
- \*5 When the wiring from the Hall output to IC Hall input is long, noise may be carried through the wiring. In this case, insert the capacitor as shown in the figure.

## Internal Equivalent Circuit



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